2SB1252

Silicon PNP epitaxial planar type darlington

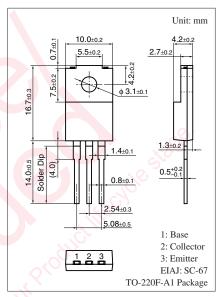
For power amplification

■ Features

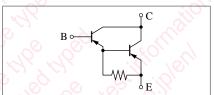
- Optimum for 35 W Hi-Fi output
- \bullet High forward current transfer ratio h_{FE}
- ullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- Full-pack package which can be installed to the heat sink with one screw.

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V_{CBO}	-120	V	
Collector-emitter voltage (Base open)	V_{CEO}	-100	V	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V	
Collector current	I_{C}	-5	A	
Peak collector current	I_{CP}	-8	A	
Collector power	P_{C}	45	W	
dissipation $T_a = 25$ °C		2		
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	



Internal Connection



■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

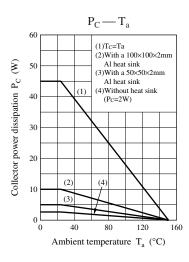
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -30 \text{ mA}, I_B = 0$	-100	35		V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -120 \text{ V}, I_E = 0$	0		-100	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -100 \text{ V}, I_B = 0$	7.7		-100	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-100	μΑ
Forward current transfer ratio	h _{FE1}	$V_{CE} = -5 \text{ V}, I_{C} = -1 \text{ A}$	2000			_
	h _{FE2} *	$V_{CE} = -5 \text{ V}, I_{C} = -4 \text{ A}$	5 000		30 000	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -4 \text{ A}, I_B = -4 \text{ mA}$			-2.5	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = -4 \text{ A}, I_B = -4 \text{ mA}$			-3.0	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time	t _{on}	$I_C = -4 \text{ A}, I_{B1} = -4 \text{ mA}, I_{B2} = 4 \text{ mA}$		1.0		μs
Storage time	t _{stg}	$V_{CC} = -50 \text{ V}$		0.8		μs
Fall time	$t_{\rm f}$			1.0		μs

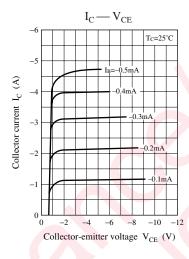
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

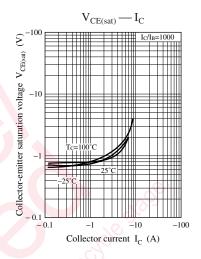
2. *: Rank classification

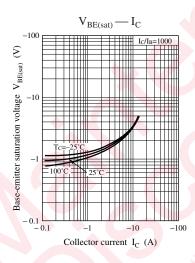
Rank	Q	Р
h _{FE2}	5 000 to 15 000	8 000 to 30 000

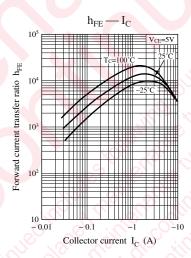
Panasonic

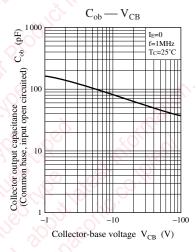


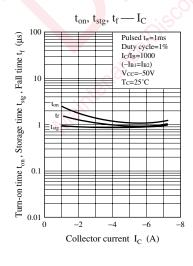


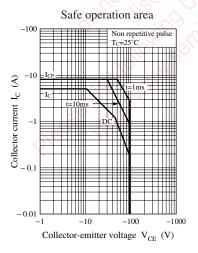


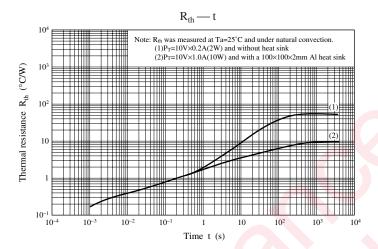












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